Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

H5551

AMPLIFIER TRANSISTOR

Collector-Emitter Voltage:Vceo=160V.

CollectorDissipation:Pc(max)=625mW

ABSOLUTE MAXIMUM RATINGS (T_a=25℃)

T_{stg}——Storage Temperature····· -55~150℃

T_j——Junction Temperature·····150℃

P_C——Collector Dissipation·····625mW

V_{CBO}——Collector-Base Voltage·····180V

V_{CEO}——Collector-Emitter Voltage·····160V

V_{EBO}——Emitter-Base Voltage·····6V

I_C——Collector Current·····600mA

TO-92

1—Emitter，E
2—Base，B
3—Collector，C

ELECTRICAL CHARACTERISTICS (T_a=25℃)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	180			V	I_C=100μA, I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	160			V	I_C=1mA, I_B=0
BV_{EBO}	Emitter-Base Breakdown Voltage	6			V	I_E=10μA， I_C=0
I_{CBO}	Collector Cut-off Current			50	nA	V_{CB}=120V, I_E=0
I_{EBO}	Emitter-Base Cut-off Current			50	nA	V_{EB}=4V, I_C=0
H_{FE}（1）	DC Current Gain	80				V_{CE}=5V, I_C=1mA
H_{FE}（2）		80		280		V_{CE}=5V, I_C=10mA
H_{FE}（3）		30				V_{CE}=5V, I_C=50mA
$V_{CE(sat1)}$	Collector- Emitter Saturation Voltage			0.15	V	I_C=10mA, I_B=-1mA
$V_{CE(sat2)}$				0.2	V	I_C=50mA, I_B=5mA
$V_{BE(sat1)}$	Base-Emitter Saturation Voltage			1	V	I_C=10mA, I_B=1mA
$V_{BE(sat2)}$				1	V	I_C=50mA, I_B=5mA,
f_T	Current Gain-Bandwidth Product	100		300	MHz	V_{CE}=10V, I_C=10mA F=100MHz